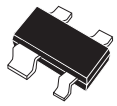
BAW100

DUAL, ISOLATED HIGH SPEED SWITCHING DIODE



SOT-143 CASE

Central™
Semiconductor Corp.

DESCRIPTION:
The CENTRAL SEMICONDUCTOR BAW100 is a Dual Isolated High Speed Switching Diode in a SOT-143 surface mount package, designed for high speed switching applications.

Marking code is CJSS.

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	85	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, tp=1 μs	I_{FSM}	4000	mA
Forward Surge Current, tp=1 ms	I_{FSM}	2000	mA
Forward Surge Current, tp=1 s	I_{FSM}	1000	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

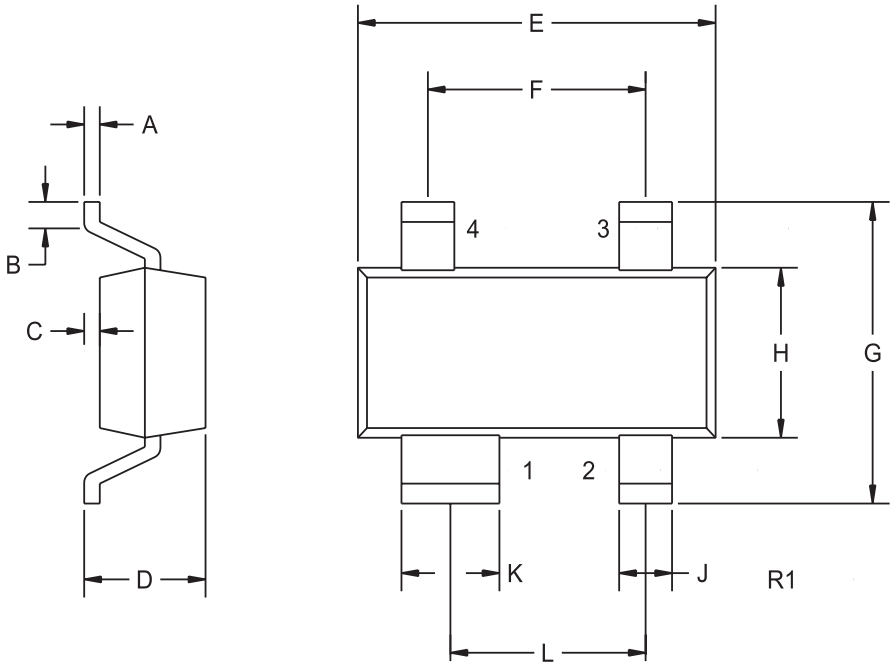
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=25V, T_A=150°C		30	μA
I_R	V_R=75V		1.0	μA
I_R	V_R=75V, T_A=150°C		50	μA
BV_R	I_R=100μA	85		V
V_F	I_F=1.0mA		715	mV
V_F	I_F=10mA		855	mV
V_F	I_F=50mA		1.00	V
V_F	I_F=150mA		1.25	V
C_T	V_R=0, f=1.0 MHz		2.0	pF
t_{rr}	I_F=I_R=10mA, R_L=100Ω, Rec. to 1.0mA		6.0	ns

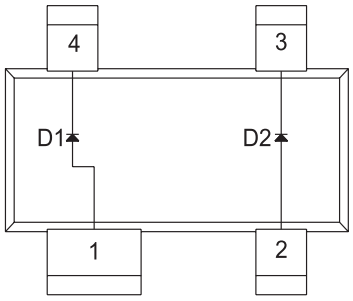
Central™
Semiconductor Corp.

BAW100

DUAL, ISOLATED HIGH SPEED SWITCHING DIODE

SOT-143 CASE - MECHANICAL OUTLINE





DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.005	0.10	0.13
B	0.006	-	0.15	-
C	0.003	0.005	0.08	0.13
D	0.037	0.043	0.94	1.09
E	0.110	0.118	2.79	3.00
F	0.079		2.01	
G	-	0.098	-	2.49
H	0.047	0.051	1.19	1.30
J	0.014	0.018	0.36	0.46
K	0.030	0.033	0.76	0.84
L	0.071		1.80	

SOT-143 (REV: R1)

LEAD CODE:
1) Anode D1
2) Anode D2
3) Cathode D2
4) Cathode D1

Marking code is CJSS.

R0 (05-April 2002)